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(54) **ELECTRONIC CIRCUIT COMPRISING A TRANSISTOR CELL**

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(57) **ABSTRACT**

An electronic circuit includes a transistor cell with multiple transistors arranged inside and on top of a semiconductor substrate. Each transistor has an active area. First insulating regions are at least partially located around the transistors and extend down to a first depth in the semiconductor substrate. Second insulating regions are positioned to insulate the active areas the transistors from one another. The second insulating regions extend down to a second depth in the semiconductor substrate, the second depth being greater than the first depth.